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ASMJP-065AUS

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	:	Todd	) Group Art Unit Unknown
App. No.	:	09/779,397	)
Filed	:	February 7, 2001	)
For	:	LOW DIELECTRIC CONSTANT MATERIALS AND PROCESSES	)
Examiner	:	Unknown	)

INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Enclosed is a form PTO-1449 listing references that are also enclosed. This Information Disclosure Statement is being filed within three months of the filing date of this application, and no fee is required in accordance with 37 C.F.R. § 1.97(b)(1).

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: April 9, 2001

By: Joseph J. Mallon

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PATENT

Case Docket No. ASMJP.065AUS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	:	Michael A. Todd
Appl. No.	:	09/779,397
Filed	:	February 7, 2001
For	:	LOW DIELECTRIC CONSTANT MATERIALS AND PROCESSES
Examiner	:	Unknown
Group Art Unit	:	Unknown

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on

April 9, 2001
(Date)

Joseph J. Mallon, Reg. No. 39,287

TRANSMITTAL LETTER

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231
ATTENTION: APPLICATION BRANCH

Dear Sir:

Enclosed for filing in the above-identified application are:

(X) An Information Disclosure Statement.

(X) A PTO Form 1449 with forty-eight (48) references.

(X) The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment, to Account No. 11-1410.

(X) Return prepaid postcard.

Joseph J. Mallon
Registration No. 39,287
Attorney of Record

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(USE SEVERAL SHEETS IF NECESSARY)

ATTY. DOCKET NO. ASMJP.065AUS	APPLICATION NO. 09/779,397
APPLICANT Michael A. Todd	
FILING DATE February 7, 2001	GROUP Unknown

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1.	4,781,942	11/01/88	Leyden et al.			
	2.	4,863,755	09/05/89	Hess et al.			
	3.	4,894,352	01/16/90	Lane et al.			
	4.	4,992,306	02/12/91	Hochberg et al.			
	5.	5,011,706	04/30/91	Tarhay et al.			
	6.	5,028,566	07/02/91	Lagendijk			
	7.	5,231,058	07/27/93	Maeda et al.			
	8.	5,240,813	08/31/93	Watanabe et al.			
	9.	5,314,724	05/24/94	Tsukune et al.			
	10.	5,324,539	06/28/94	Maeda et al.			
	11.	5,380,555	01/10/95	Mine et al.			
	12.	5,433,786	07/18/95	Hu et al.			
	13.	5,494,712	02/27/96	Hu et al.			
	14.	5,554,570	09/10/96	Maeda et al.			
	15.	5,563,105	10/08/96	Dobuzinsky et al.			
	16.	5,703,404	12/30/97	Matsuura			
	17.	5,840,821	11/24/98	Nakano et al.			
	18.	5,876,798	03/02/99	Vassiliev			
	19.	5,989,998	11/23/99	Sugahara et al.			
	20.	5,998,522	12/07/99	Nakano et al.			
	21.	6,045,877	04/04/00	Gleason et al.			
	22.	6,051,321	04/18/00	Lee et al.			
	23.	6,051,508	04/18/00	Takase et al.			
	24.	6,054,379	04/25/00	Yau et al.			
	25.	6,068,884	05/30/00	Rose et al.			

EXAMINER	DATE CONSIDERED

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMJP.065AUS	APPLICATION NO. 09/779,397
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	APPLICANT Michael A. Todd	
	FILING DATE February 7, 2001	GROUP Unknown

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
	26.	WO 97/40207	10/30/97	PCT			X	
	27.	WO 99/55526	11/04/99	PCT			X	
	28.	EPO 367 004 B1	12/15/93	EPO			X	
	29.	EP 0 436 185 B1	03/20/96	EPO			X	
	30.	EP 0 723 600 B1	07/07/99	EPO			X	
	31.	EP 0 771 886 A1	05/07/97	EPO			X	
	32.	EP O 935 283 A2	08/11/99	EPO			X	
	33.	EP 0 960 958 A2	12/01/99	EPO			X	

EXAMINER INITIAL		OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
	34.	Bayer et al., *Overall kinetics of SiOx remote-PECVD using different organosilicon monomers,* Surface and Coatings Technology, 116-119 (1999) 874-878
	35.	Berjoan et al., *XPS and XPS valence band characterizations of amorphous or polymeric silicon based thin films prepared by PACVD from organosilicon monomers,* J. Phys. IV France 9 (1999) pp. 1059-1068.
	36.	Constant et al., *Some Properties of amorphous SiXC1-x (H) alloys prepared by CVD from various organosilicon compounds,*Solid State Chemistry, 1982, pp. 267-270
	37.	Deville et al., *An AES study of the influence of carbon on the chemical structure of some oxide films deposited by PECVD of organosilicon precursors,* Applied Surface Science 137 (1999) 136-141
	38.	Fonseca et al., *Plasma Polymerization of Tetramethylsilane,* Am. Chemical Society, 1993, 5, 1676-1682
	39.	Inoue et al., *Mass spectroscopy in plasma-enhanced chemical vapor deposition of silicon-oxide films using tetramethoxylsilane,* Thin Solid Films 316 (1998) 79-84
	40.	Inoue et al., *Spectroscopic studies on preparation of silicon oxide films by PECVD using organosilicon compounds,* Plasma Sources Sci. Technol. 5 (1996) 339-343
	41.	Loboda, M.J., *New solutions for intermetal dielectrics using trimethylsilane-based PECVD processes,* Microelectronic Enginering 50 (2000) 15-23
	42.	Nguyen et al., *Plasma organosilicon polymers,* J. Electrochem. Soc., August 1985, pp. 1925-1932
	43.	Shirafuji et al., *PE-CVD of Fluorocarbon/SiO composite thin films using C4F8 and HMDSO1,* Plasmas and Polymers, Vo. 4, No. 1, 1999, pp. 57-75
	44.	Shirafuji et al., *PE-CVD of fluorocarbon/silicon oxide composite thin films from TFE and HMDSO,* Mat. Res. Soc. Symp. Proc. Vol. 544, pp. 173-178
	45.	Shirafuji et al., *Plasma copolymerization of tetrafluoroethylene/hexamethyldisiloxane and In Situ Fourier Transform infrared spectroscopy of its gas phase,* Jpn. J. Appl. Phys. Vol. 38 (1999) pp. 4520-4526
	46.	Sugahara et al., *Low Dielectric constant carbon containing SiO2 films deposited by PECVD technique using a novel CVD precursor,* DUMIC Conference, Feb. 10-11, 1997, pp. 19-25
	47.	Thomas et al., *Plasma etching and surface analysis of a SiC:H films deposited by low temperature plasma enhanced chemical vapor deposition,* Mat. Res. Soc. Symp. Proc. Vo. 334, 1994, pp. 445-450
	48.	Matsuki, N., U.S. Patent Application No. 09/243,156 *Silicone Polymer insulation film on semiconductor substrate and method for forming the film,* filed February 2, 1999.

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EXAMINER	DATE CONSIDERED

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